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Chae (43) **Pub. Date: May 5, 2005**(54) **ARRAY SUBSTRATE FOR USE IN IN-PLANE
SWITCHING MODE LIQUID CRYSTAL
DISPLAY DEVICE AND METHOD OF
FABRICATING THE SAME**(30) **Foreign Application Priority Data**

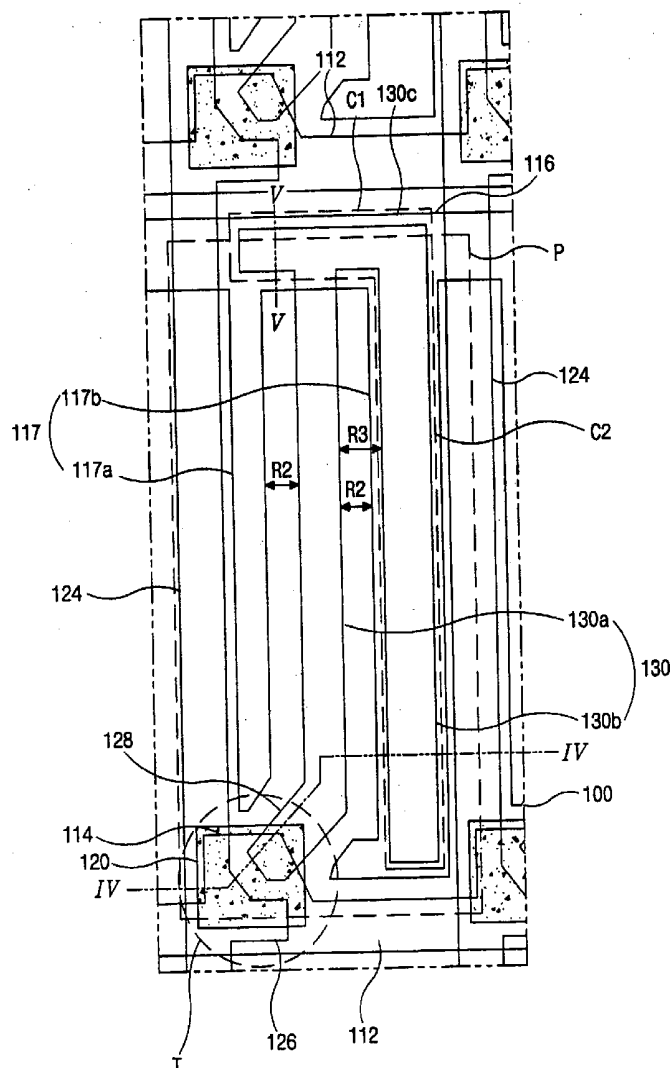
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Publication Classification(76) **Inventor: Gee Sung Chae, Yoonsu-gu (KR)**(51) **Int. Cl.⁷ G02F 1/1343**(52) **U.S. Cl. 349/141**

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**MCKENNA LONG & ALDRIDGE LLP
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WASHINGTON, DC 20006 (US)**(57) **ABSTRACT**

The present invention is related to an IPS-LCD device and a method of fabricating an array substrate for use in the IPS-LCD device, which increase a high aperture ratio and provide a large and enough storage capacitance. A common line formed of an opaque metal is designed to have a small width for the increased aperture ratio. A portion of a pixel electrode overlaps one of common electrodes, thereby forming a supplementary storage capacitor. As a result, with a main storage capacitor comprised of a portion of pixel electrode and a portion of common line, the array substrate of the present invention can have two storage capacitors. A sufficient and satisfactory capacitance can be obtained and the aperture ratio is raised.

(21) **Appl. No.: 11/003,397**(22) **Filed: Dec. 6, 2004****Related U.S. Application Data**(62) **Division of application No. 10/325,873, filed on Dec. 23, 2002.**

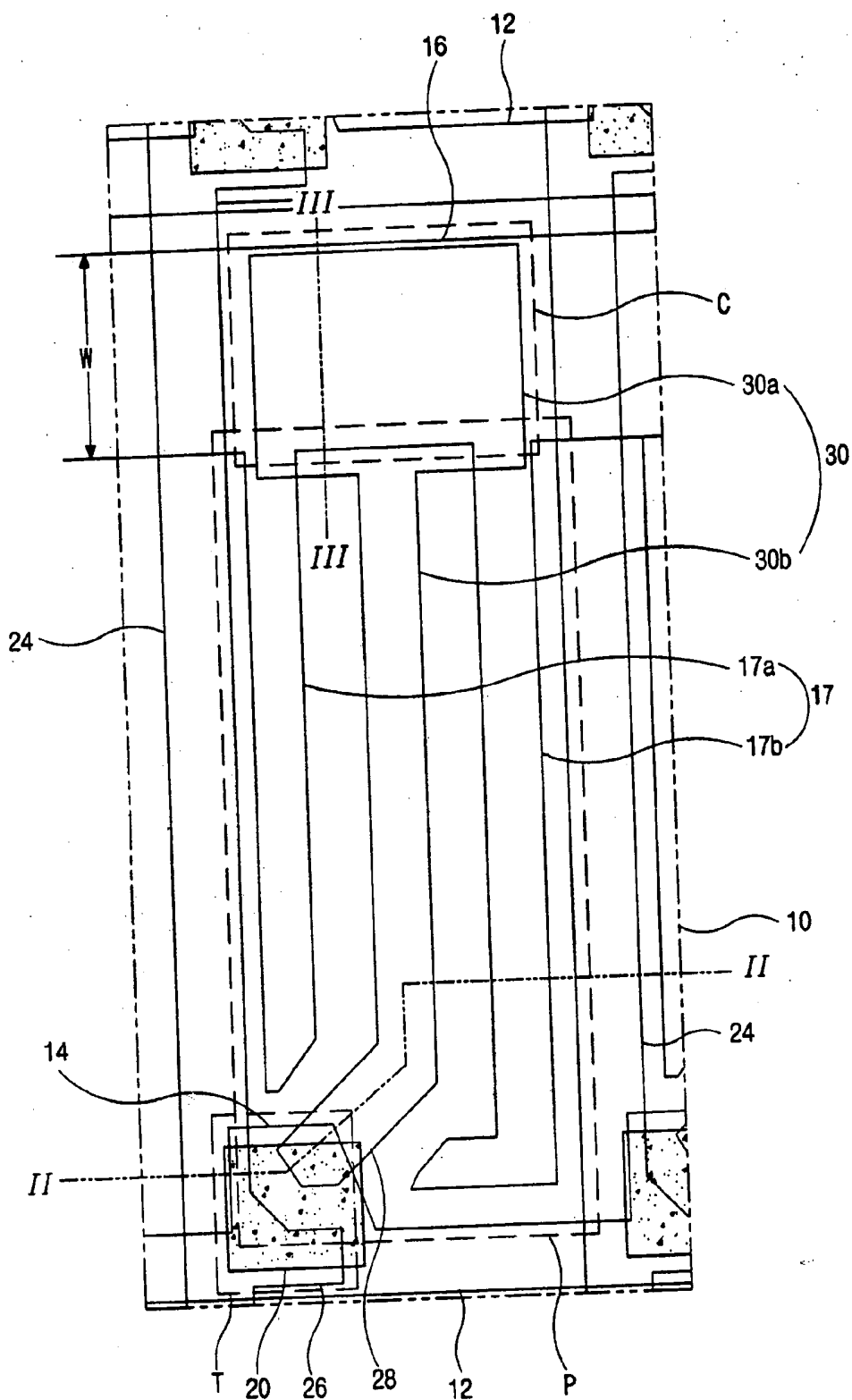


FIG. 1
(Related Art)

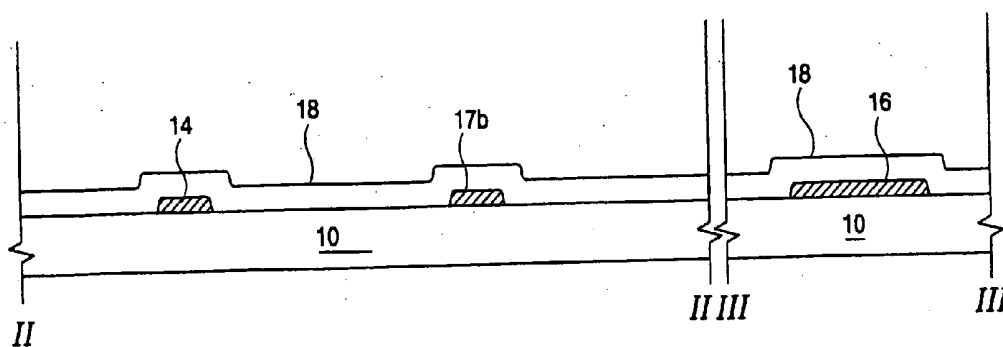


FIG 2A
(Related Art)

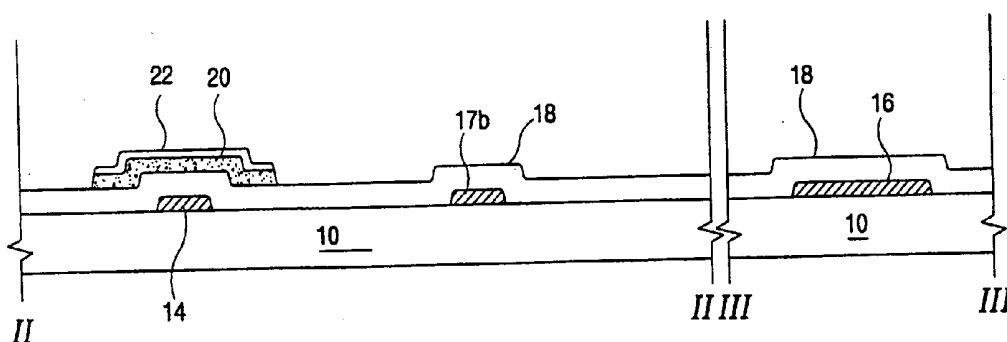


FIG 2B
(Related Art)

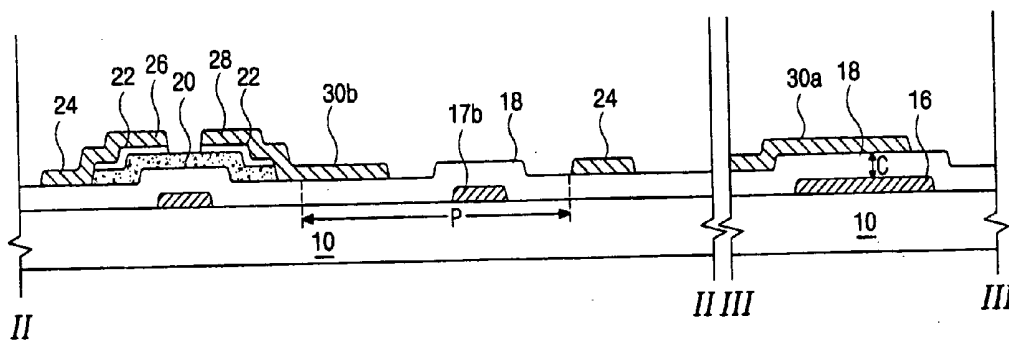


FIG 2C
(Related Art)

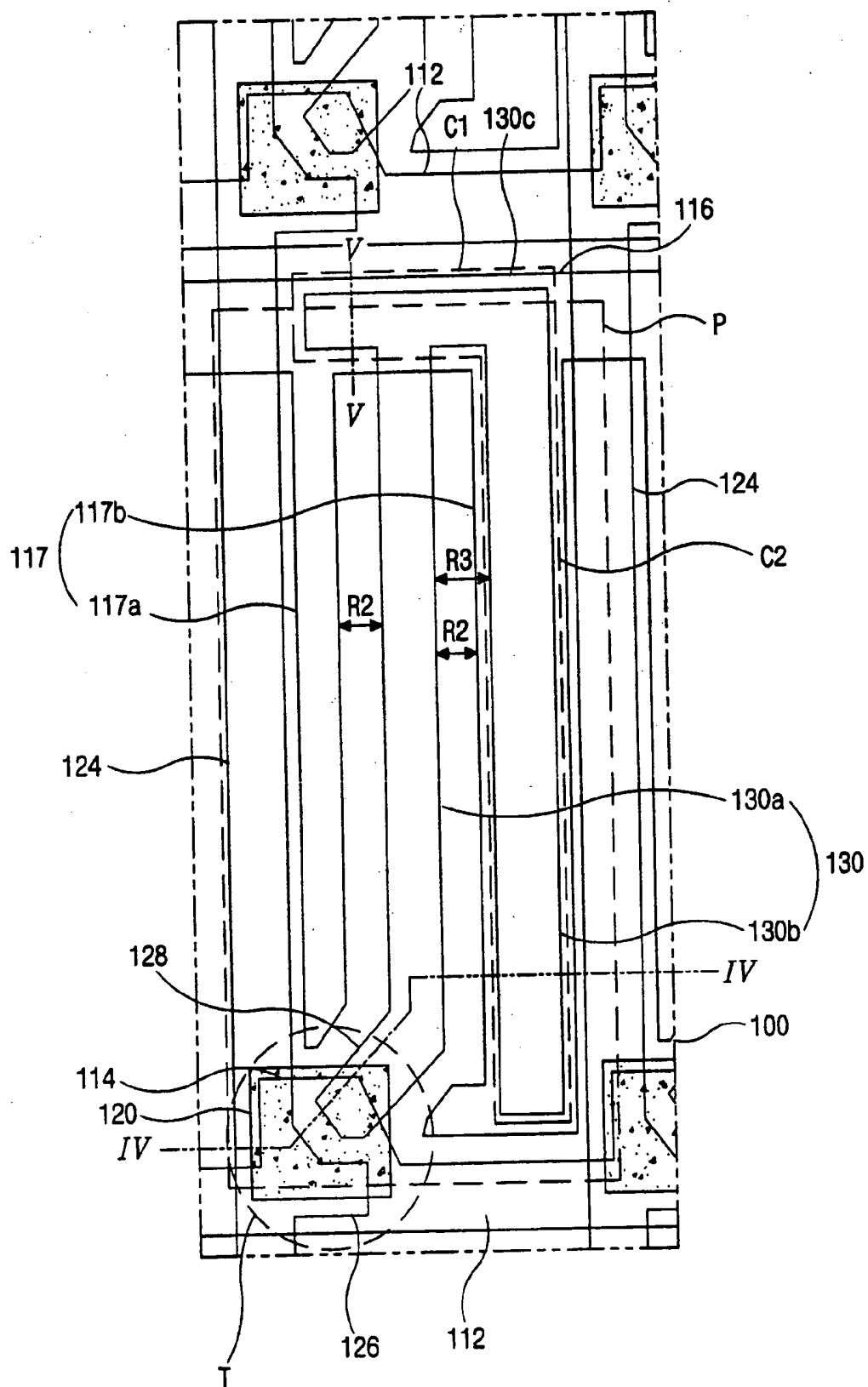


FIG 3

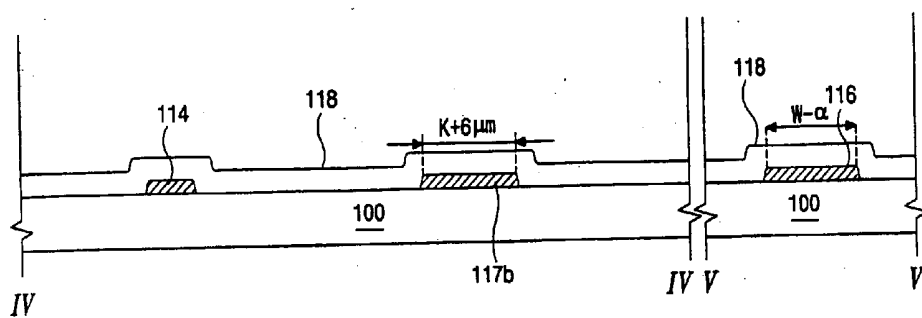


FIG 4A

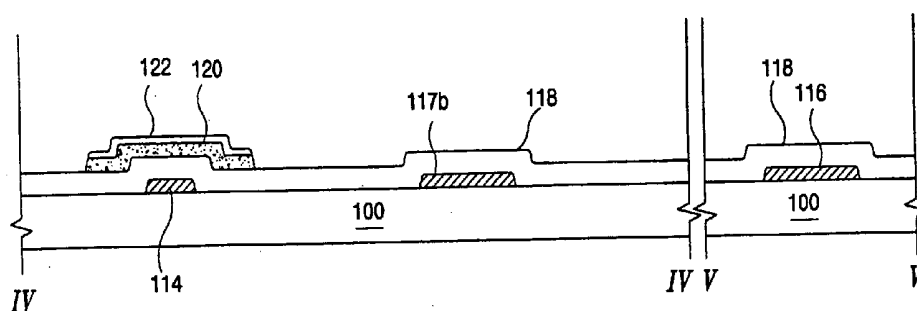


FIG 4B

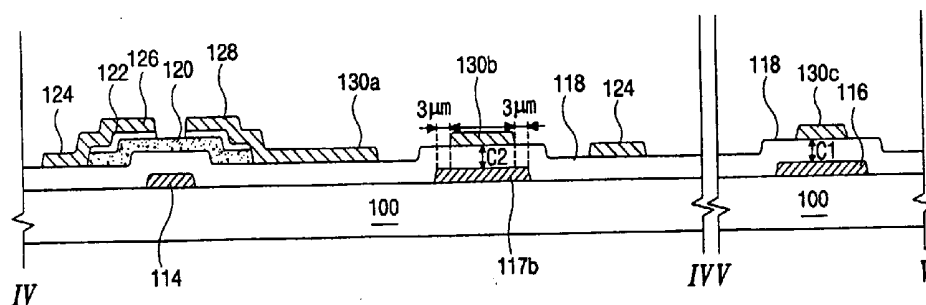


FIG 4C

ARRAY SUBSTRATE FOR USE IN IN-PLANE SWITCHING MODE LIQUID CRYSTAL DISPLAY DEVICE AND METHOD OF FABRICATING THE SAME

[0001] This application claims the benefit of Korean Patent Application No. 2001-0087401, filed on Dec. 28, 2001, which is hereby incorporated by reference for all purposes as if fully set forth herein.

BACKGROUND OF THE INVENTION

[0002] 1. Field of the Invention

[0003] The present invention relates to a liquid crystal display (LCD) device, and more particularly, to an array substrate for use in an in-plane switching mode liquid crystal display device (IPS-LCD).

[0004] 2. Description of the Related Art

[0005] A liquid crystal display device uses the optical anisotropy and polarization properties of liquid crystal molecules to produce an image. Liquid crystal molecules have a definite alignment direction as a result of their long, thin shapes. That alignment direction can be controlled by an applied electric field. In other words, as the direction of an applied electric field changes, so does the alignment of the liquid crystal molecules. Due to the optical anisotropy, the refraction of incident light depends on the alignment direction of the liquid crystal molecules. Thus, by properly controlling an applied electric field, a desired light image can be produced.

[0006] Of the different types of known LCDs, active matrix LCDs (AM-LCDs), which have thin film transistors and pixel electrodes arranged in a matrix form, are the subject of significant research and development because of their high resolution and superiority in displaying moving images.

[0007] LCD devices have wide application in office automation (OA) equipment and video units because they are light and thin and have low power consumption characteristics. The typical liquid crystal display (LCD) panel has an upper substrate, a lower substrate and a liquid crystal layer interposed therebetween. The upper substrate, commonly referred to as a color filter substrate, usually includes a common electrode and color filters. The lower substrate, commonly referred to as an array substrate, includes switching elements, such as thin film transistors (TFTs) and pixel electrodes.

[0008] As previously described, LCD device operation is based on the principle that the alignment direction of the liquid crystal molecules is dependent upon an electric field applied between the common electrode and the pixel electrode. Thus, the alignment direction of the liquid crystal molecules is controlled by the application of an electric field to the liquid crystal layer. When the alignment direction of the liquid crystal molecules is properly adjusted, incident light is refracted along the alignment direction to display image data. The liquid crystal molecules function as an optical modulation element having variable optical characteristics that depend upon polarity of the applied voltage.

[0009] In a conventional LCD device, since the pixel and common electrodes are positioned on the lower and upper substrates, respectively, the electric field induced between

them is perpendicular to the lower and upper substrates. However, the conventional LCD devices having the longitudinal electric field have a drawback in that they have a very narrow viewing angle. In order to solve the problem of narrow viewing angle, in-plane switching liquid crystal display (IPS-LCD) devices have been proposed. The IPS-LCD devices typically include a lower substrate where a pixel electrode and a common electrode are disposed, an upper substrate having no electrode, and a liquid crystal interposed between the upper and lower substrates. A detailed explanation about the lower substrate (i.e., array substrate) of the IPS-LCD device will be provided referring to figures.

[0010] FIG. 1 is a plan view illustrating one pixel of an array substrate of an in-plane switching mode liquid crystal display (IPS-LCD) device according to a related art. As shown, gate lines 12 are transversely disposed on a substrate (see reference element 10 of FIG. 2A). A common line 16 is spaced apart from the gate lines 12, and disposed adjacent to and parallel with the gate lines 12. Data lines 24 that are spaced apart from each other are disposed across and substantially perpendicular to the gate and common lines 12 and 16. A pair of data lines 24 and a pair of gate and common lines 12 and 16 define a pixel area P.

[0011] A switching device, e.g., a thin film transistor T, is positioned near the crossing of the gate and data lines 12 and 24. As shown in FIG. 1, the thin film transistor T includes a gate electrode 14, an active layer 20, a source electrode 26 and a drain electrode 28. The gate and source electrodes 14 and 26 are positioned and electrically connected with the gate and data lines 12 and 24, respectively. Namely, the gate electrode 14 extends from the gate line 12, while the source electrode 26 extends from the data line 24. The drain electrode 28 is spaced apart from the source electrode 26 and overlaps a portion of the active layer 20. The active layer 20 is located right above the gate electrode 14 and under the source and drain electrodes 26 and 28. Thus, the source electrode 26 and the drain electrode 28 overlap portions of the active layer 20, respectively.

[0012] In the pixel area P, a pixel electrode 30 connected to the drain electrode 28 is disposed. The pixel electrode 30 includes a horizontal portion 30a above the common line 16 and a vertical portion 30b parallel with the data lines 24. The horizontal and vertical portions 30a and 30b and the drain electrode 28 are formed as one united body. A common electrode 17 including first and second common electrodes 17a and 17b is also disposed in the pixel area P. The first and second common electrodes 17a and 17b extend from the common line 16 and are formed as one united body with the common line 16. The first and second common electrodes 17a and 17b are parallel with and adjacent to the data lines 24, respectively. Between the first and second common electrodes 17a and 17b, the vertical portion 30b of the pixel electrode 30 is positioned.

[0013] There is a storage capacitor C that is parallel-connected to the pixel at the top of the pixel area P. The storage capacitor C is formed of a portion of the common line 16, a horizontal portion 30a of the pixel electrode 30, and a dielectric layer (not shown). Namely, the portion of the common line 16 acts as a first electrode and the horizontal portion 30a of the pixel electrode 30 acts as a second electrode in the storage capacitor C. The common line 16 in

the related art shown in FIG. 1 has a width W. When designing the common line 16 to have the width W, the width W of the related art should be as large as necessary so that the signal can easily flow through the common line 16 and the storage capacitor C can have an enough capacitance.

[0014] FIGS. 2A to 2C are cross sectional views taken along lines II-II and III-III of FIG. 1 and illustrate fabricating processes for the array substrate.

[0015] Referring to FIG. 2A, a first metal layer is formed on a substrate 10 and then patterned to form the gate line 12 (see FIG. 1), the gate electrode 14, the common line 16, and the first and second common electrodes 17a and 17b. Aluminum (Al), aluminum alloy (e.g., aluminum neodymium (AlNd)), chromium (Cr), molybdenum (Mo) or tungsten (W) is used as a material for the first metal layer. The gate electrode 14 protrudes from the gate line 12 (see FIG. 1). The common line 16 is adjacent to and parallel with the gate line. Further, the common line 16 is spaced apart from the gate line by a predetermined distance. As mentioned before, the first and second common electrodes 17a and 17b extend from the common line 16 and are disposed parallel with and adjacent to the data lines that are formed in a later step. Thereafter, a gate insulation layer 18 is formed on entire surface of the substrate 10 to cover the patterned first metal layer. Thus, for example, as shown in FIG. 2A, the gate electrode 14, the second common electrode 17b and the common line 16 are covered by the gate insulation layer 18. The gate insulation layer 18 is an inorganic material, such as silicon nitride (SiN_x).

[0016] In FIG. 2B, an amorphous silicon layer (a-Si: H) and an impurity-included amorphous silicon layer (n^+ a-Si: H) are sequentially formed on the gate insulation layer 18 and then patterned to form the active layer 20 and an ohmic contact layer 22. Particularly, the active layer 20 and the ohmic contact layer 22 are formed right above the gate electrode 14. Since the amorphous silicon layer (a-Si: H) and the impurity-included amorphous silicon layer (n^+ a-Si: H) are simultaneously patterned, the active layer 20 is interposed between the ohmic contact layer 22 and the gate insulation layer 18.

[0017] Now in FIG. 2C, a second metal layer is formed on entire surface of the gate insulation layer 18 and then patterned to form the data lines 24, the source electrode 26, the drain electrode 28 and the pixel electrode 30 (including the horizontal portion 30a and the vertical portion 30b). As with the first metal layer, the second metal layer is one of chromium (Cr), aluminum (Al), aluminum alloy (e.g., AlNd), molybdenum (Mo), and the like. As shown and mentioned with reference FIG. 1, the data lines 24 cross both the gate line 12 and the common line 16, and define the pixel area P with both the gate line 12 and the common line 16. The source electrode 26 extends from the data line 24 and overlaps a portion of the ohmic contact layer 20. The horizontal portion 30a of the pixel electrode 30 is formed above the common line 16 to overlap a portion of the common line 16. The vertical portion 30b of the pixel electrode 30 extends from the horizontal portion 30a to the pixel area P and is disposed between the first and second common electrodes 17a and 17b parallel with the data lines. At the end of the vertical portion 30b of the pixel electrode 30, the drain electrode 28 is formed to overlap a portion of the ohmic contact layer 22. Since the source and drain

electrodes 26 and 28 are spaced apart from each other, a portion of the ohmic contact layer 22 is removed using the source and drain electrodes 26 and 28 as a mask. Thus, a channel region is formed in the active layer 20 between the source and drain electrodes 26 and 28. The portion of the common line 16 and the horizontal portion 30a form the storage capacitor C. As mentioned before, the portion of the common line 16 acts as a first electrode of the storage capacitor, the horizontal portion 30a of the pixel electrode 30 acts as a second electrode of the storage capacitor, and the gate insulation layer 18 between the common line 16 and the horizontal portion 30a acts as a dielectric layer.

[0018] According to aforementioned structure of the array substrate shown in FIGS. 1 and 2A-2C, the array substrate for the IPS-LCD device has only one storage capacitor in the pixel. Thus, the common line acting as a first storage electrode needs to be designed to have large width for sufficient and satisfactory capacitance. In this case, since the common line is formed of an opaque material, the aperture ratio of the pixel becomes decreased.

SUMMARY OF THE INVENTION

[0019] Accordingly, the present invention is directed to an IPS-LCD device that substantially obviates one or more of the problems due to limitations and disadvantages of the related art.

[0020] An advantage of the present invention is to provide a method of fabricating an array substrate for use in the IPS-LCD device (as well as the array substrate itself), which have a common line having a small width to increase the aperture ratio.

[0021] Another advantage of the present invention is to provide the method of fabricating the array substrate (as well as the array substrate itself) for use in the IPS-LCD device, which is designed to have an additional storage capacitor for the increase of capacitance.

[0022] Additional features and advantages of the invention will be set forth in the description, which follows, and in part will be apparent from the description, or may be learned by practice of the invention. The objectives and other advantages of the invention will be realized and attained by the structure particularly pointed out in the written description and claims hereof as well as the appended drawings.

[0023] To achieve these and other advantages and in accordance with the purpose of the present invention, as embodied and broadly described, an embodiment of the present invention provides an array substrate for use in an IPS-LCD device, including: a gate line on a substrate and disposed in a first direction; a common line on the substrate; first and second common electrodes substantially perpendicularly extending from the common line; a gate insulation layer formed on the substrate to cover the gate line, the common line and the first and second common electrodes; a data line formed on the gate insulation layer and disposed in a second direction substantially perpendicularly crossing both the gate line and the common line to define a pixel area; a pixel electrode on the gate insulation layer, the pixel electrode having first, second and third portions, wherein the first portion is disposed between the first and second common electrodes, the second portion is disposed overlapping

the second common electrode, and the third portion is disposed above the common line; and a thin film transistor at a crossing of the gate and data lines, the thin film transistor having a gate electrode, an active layer, a source electrode and a drain electrode. According to the array substrate of the present invention, a width of the second common electrode overlapped by the second portion of the pixel electrode is larger than that of the second portion of the pixel electrode by about 6 micrometers. A distance between the first and second portions of the pixel electrode is larger by about 3 micrometers than a distance between the first portion of the pixel electrode and the second common electrode. An end of the first portion is connected to the drain electrode of the thin film transistor. The thin film transistor further includes an ohmic contact layer on the active layer. The source electrode extends from the data line, the gate electrode extends from the gate line, the drain electrode extends from the first portion of the pixel electrode, the active layer is disposed above the gate electrode, and the ohmic contact layer is interposed between the active layer and the source and drain electrodes. The gate electrode, the gate line, the common line, the first and second common electrode, the source and drain electrodes, the data line, and the pixel electrode include one of aluminum (Al), aluminum alloy (Al alloy), chromium (Cr), molybdenum (Mo), and tungsten (W). The common line and the first and second common electrodes are formed as one united body. The pixel electrode and the drain electrode are formed as one united body. The third portion of the pixel electrode and a portion of the common line form a first storage capacitor with the gate insulation layer interposed therebetween. The second portion of the pixel electrode and the second common electrode form a second storage capacitor with the gate insulation layer interposed therebetween.

[0024] In another aspect of the present invention is to provide a method of fabricating an array substrate for use in an IPS-LCD device. According to the present invention, the method include: forming a gate line, a gate electrode, a common line and first and second common electrode on a substrate using a first metal layer, wherein the gate and common lines are disposed in a first direction; forming a gate insulation layer on entire surface of the substrate to cover the first metal layer; forming an active layer on the gate insulation layer and an ohmic contact layer on the active layer using an amorphous silicon and impurity-doped amorphous silicon; forming a data line, a source electrode, a drain electrode and a pixel electrode using a second metal layer, wherein the data line is disposed on the gate insulation layer in a second direction substantially perpendicularly crossing both the gate line and the common line to define a pixel area, wherein the source and drain electrode are disposed on the ohmic contact layer and spaced apart from each other, and wherein the pixel electrode is disposed on the gate insulation layer and includes a first portion that is disposed between the first and second common electrodes, a second portion that is disposed overlapping the second common electrode, and a third portion that is disposed above the common line; and forming a thin film transistor at a crossing of the gate and data lines, the thin film transistor having the gate electrode, the active layer, the ohmic contact layer, the source electrode and the drain electrode. A width of the second common electrode overlapped by the second portion of the pixel electrode is larger than that of the second portion of the pixel electrode by about 6 micrometers. A distance between the

first and second portions of the pixel electrode is larger than a distance between the first portion of the pixel electrode and the second common electrode by about 3 micrometers. An end of the first portion is connected to the drain electrode of the thin film transistor. The source electrode extends from the data line, the gate electrode extends from the gate line, the drain electrode extends from the first portion of the pixel electrode, the active layer is disposed right above the gate electrode, and the ohmic contact layer interposed between the active layer and the source and drain electrodes. The first and second metal layers are formed of one of aluminum (Al), aluminum alloy (Al alloy), chromium (Cr), molybdenum (Mo), and tungsten (W). The common line and the first and second common electrodes are formed as one united body. The pixel electrode and the drain electrode are formed as one united body. The third portion of the pixel electrode and a portion of the common line form a first storage capacitor with the gate insulation layer interposed therebetween. The second portion of the pixel electrode and the second common electrode form a second storage capacitor with the gate insulation layer interposed therebetween.

[0025] It is to be understood that both the foregoing general description and the following detailed description are exemplary and explanatory and are intended to provide further explanation of the invention as claimed.

BRIEF DESCRIPTION OF THE DRAWINGS

[0026] For a more complete understanding of the present invention and the advantages thereof, reference is now made to the following descriptions taken in conjunction with the accompanying drawings, in which like reference numerals denote like parts, and in which:

[0027] FIG. 1 is a plan view illustrating one pixel of an array substrate of an in-plane switching mode liquid crystal display (IPS-LCD) device according to a related art;

[0028] FIGS. 2A to 2C are cross sectional views taken along lines II-II and III-III of FIG. 1 and illustrate fabricating processes for the array substrate;

[0029] FIG. 3 is a plan view illustrating one pixel of an array substrate of an in-plane switching mode liquid crystal display (IPS-LCD) device according to an embodiment; and

[0030] FIGS. 4A to 4C are cross-sectional views taken along lines IV-IV and V-V of FIG. 3 and illustrate fabricating processes for the array substrate according to the embodiment illustrated in FIG. 3.

DETAILED DESCRIPTION OF THE ILLUSTRATED EMBODIMENT

[0031] Reference will now be made in detail to an illustrated embodiment of the present invention, an example of which is shown in the accompanying drawings. Wherever possible, similar reference numbers will be used throughout the drawings to refer to the same or similar parts.

[0032] FIG. 3 is a plan view illustrating one pixel of an array substrate of an in-plane switching mode liquid crystal display (IPS-LCD) device according to an embodiment of the present invention. As shown, gate lines 112 are transversely disposed on a substrate (see reference element 100 of FIG. 4A). A common line 116 is spaced apart from and disposed parallel with and adjacent to the gate lines 112.

Data lines **124** that are spaced apart from each other are disposed across and substantially perpendicular to the gate and the common lines **112** and **116**. A pair of gate and common lines **112** and **116** and a pair of data lines **124** define a pixel area P.

[0033] A switching device, e.g., a thin film transistor (TFT), which is indicated by a portion T, is positioned near the crossing of the gate and data lines **112** and **124**. As shown in **FIG. 3**, the thin film transistor T includes a gate electrode **114**, an active layer **120**, a source electrode **126** and a drain electrode **128**. The gate and source electrodes **114** and **126** are positioned and electrically connected with the gate and data lines **112** and **124**, respectively. The drain electrode **128** is spaced apart from the source electrode **126** and overlaps one portion of the gate electrode **114**. The source electrode **126** also overlaps the other portion of the gate electrode **114**. An active layer **120** is located right above the gate electrode **114** and under the source and drain electrodes **126** and **128**. The active layer **120** may be located right above the gate electrode **114**.

[0034] In the pixel area P, a common electrode **117** including first and second common electrodes **117a** and **117b** is disposed substantially parallel with the data lines **124**. The first and second common electrodes **117a** and **117b** are adjacent to the data lines **124**, respectively. The first and second common electrodes **117a** and **117b** extend from the common line **116** and are formed as one united body with the common line **116**. In the present invention, the second common electrode **117b** has a larger width than the first common electrode **117a**.

[0035] Still referring to **FIG. 3**, a pixel electrode **130** including first, second and third portions **130a**, **130b** and **130c** is disposed in the pixel area P. The first and second portions **130a** and **130b** are substantially parallel with the data lines **124**. The first portion **130a** of the pixel electrode **130** is disposed between the first and second common electrodes **117a** and **117b**, while the second portion **130b** of the pixel electrode **130** is disposed above the second common electrode **117b** to overlap the second common electrode **117b**. The second portion **130b** of the pixel electrode **130** may be disposed right above the second common electrode **117b**. In the present invention, a width of the second portion **130b** of the pixel electrode **130** is smaller than that of the second common electrode **117b**. The first portion **130a** of the pixel electrode **130** is connected to the drain electrode **128** of the thin film transistor T. The third portion **130c** of the pixel electrode **130** is disposed above the common line **116** and connects the first portion **130a** to the second portion **130b** so that the first and second portions **130a** and **130b** are in a shape of extending from the third portion **130c**.

[0036] In the present invention shown in **FIG. 3**, the width of the second common electrode **117b** is larger than that of the second portion **130b** of the pixel electrode **130** by about 3 micrometers on both sides. Further, the distances R2 between the first portion **130a** of the pixel electrode **130** and the first and second common electrodes **117a** and **117b** are the same. Moreover, the second portion **130b** does not act as a pixel electrode actually, but constitutes a supplementary storage capacitor C2 with the second common electrode **117b**. Namely, the second common electrode **117b** acts as a first capacitor electrode, and the second portion **130b** of the pixel electrode **130** acts as a second capacitor electrode in

the supplementary storage capacitor C2. In the structure shown in **FIG. 3**, a distance R3 between the first and second portions **130a** and **130b** of the pixel electrode **130** is larger than the distance R2 by about 3 micrometers because the second portion **130b** of the pixel electrode **130** is smaller than the second common electrode **117b** by 6 micrometers (3 micrometers on both sides). Although the first portion **130a** and the second portion **130b** of the pixel electrode **130** are formed in the same plane using the same material, the second portion **130b** does not electrically interfere with the first portion **130a** because the distance R3 between the first and second portions **130a** and **130b** is larger by about 3 micrometers than the distance R2 between the first portion **130a** and the second common electrode **117b**, where the electric field is generated. Namely, the first and second portions **130a** and **130b** do not affect to each other. Accordingly, the electric field is only generated in intervals between the first portion **130a** of the pixel electrode **130** and the first common electrode **117a** and between the first portion **130a** of the pixel electrode **130** and the second common electrode **117b**.

[0037] Furthermore, the third portion **130c** of the pixel electrode **130** forms a main storage capacitor C1 with the common line **116** at a top of the pixel area P. The storage capacitor C1 is comprised of a portion of the common line **116**, the third portion **130c** of the pixel electrode **130**, and a dielectric layer (not shown). Thus, the portion of the common line **116** acts as a first electrode and the third portion **130c** of the pixel electrode **130** acts as a second electrode in the storage capacitor C1. According to the aforementioned inventive structure of the array substrate shown in **FIG. 3**, a width of the common line **116** is smaller than the width W of the related art IPS-LCD illustrated in **FIG. 1** because the main storage capacitor C1 does not need to have a large capacitance. Since the array substrate of **FIG. 3** has the supplementary storage capacitor C2 in the pixel area, the common line **116** does not have to be designed to have a larger width. Namely, there are two storage capacitors C1 and C2 in the array substrate of the present invention. Since the common line **116** of the present invention has a small width rather than that of the related art, the high aperture ratio can be achieved in the present invention.

[0038] **FIGS. 4A** to **4C** are cross-sectional views taken along lines IV-IV and V-V of **FIG. 3** and illustrate fabricating processes for the array substrate according to an embodiment of the present invention.

[0039] Referring to **FIG. 4A**, a first metal layer is formed on a transparent substrate **100** and then patterned to form the gate line **112** (see **FIG. 3**), the gate electrode **114**, the common line **116**, and the first and second common electrodes **117a** and **117b**. Aluminum (Al), aluminum alloy (e.g., aluminum neodymium (AlNd)), chromium (Cr), molybdenum (Mo), tungsten (W) or the like is used as a material for the first metal layer. The gate electrode **114** protrudes from the gate line **112** (see **FIG. 3**). The common line **116** is adjacent to and substantially parallel with the gate line. Further, the common line **116** is spaced apart from the gate line by a predetermined distance. At this time of forming the common line **116**, the common line **116** is designed to have a width that is smaller than the related art width W (see **FIG. 1**) by alpha (α) (i.e., $W-\alpha$). The first and second common electrodes **117a** and **117b** extend from the common line **116** and are disposed substantially parallel with and adjacent to

the data lines that are formed in a later step. When designing the first and second common electrodes **117a** and **117b**, the second common electrode **117b** is designed to have a width $K+6$ that is larger than a width K of the first common electrode **117a** by about 6 micrometers.

[0040] After forming and patterning the first metal layer on the transparent substrate **100**, a gate insulation layer **118** is formed on entire surface of the transparent substrate **100** to cover the patterned first metal layer. Thus, for example, as shown in **FIG. 4A**, the gate electrode **114**, the second common electrode **117b** having the width $K+6$ and the common line **116** having the width $W-\alpha$ are covered by the gate insulation layer **118**. The gate insulation layer **118** is an inorganic material, such as silicon nitride (SiN_x) or silicon oxide (SiO_x).

[0041] In **FIG. 4B**, an amorphous silicon layer (a-Si: H) and an impurity-doped amorphous silicon layer (n^+ a-Si: H) are sequentially formed on the gate insulation layer **118** and then patterned to form the active layer **120** and an ohmic contact layer **122**. Particularly, the active layer **120** and the ohmic contact layer **122** are formed above the gate electrode **114**. Since the amorphous silicon layer (a-Si: H) and the impurity-doped amorphous silicon layer (n^+ a-Si: H) are simultaneously patterned, the active layer **120** is interposed between the ohmic contact layer **122** and the gate insulation layer **118**.

[0042] In **FIG. 4C**, a second metal layer is formed on entire surface of the gate insulation layer **118** and then patterned to form the data lines **124**, the source electrode **126**, the drain electrode **128** and the pixel electrode **130** (including the first, second and third portions **130a**, **130b** and **130c**). As with the first metal layer, the second metal layer is one of chromium (Cr), aluminum (Al), aluminum alloy (e.g., AlNd), molybdenum (Mo), and the like. As shown and mentioned with reference **FIG. 3**, the data lines **124** cross both the gate line **112** and the common line **116**, and define the pixel area P with both the gate line **112** and the common line **116**. The source electrode **126** extends from the data line **124** and overlaps a portion of the ohmic contact layer **120**. The third portion **130a** of the pixel electrode **130** is formed above the common line **116** to overlap a portion of the common line **116**. The third portion **130a** of the pixel electrode **130** may be formed right above the common line **116**. The third portion **130a** of the pixel electrode **130**, the common line **116** and the interposed gate insulation layer **118** form the main storage capacitor **C1**. The first and second portions **130a** and **130b** of the pixel electrode **130** extend from the third portion **130c** of the pixel electrode **130** substantially parallel with the data lines **124**, as shown in **FIG. 3**. At the end of the first portion **130a** of the pixel electrode **130**, the drain electrode **128** is formed overlapping a portion of the ohmic contact layer **122**. The first portion **130b** of the pixel electrode **130** is disposed between the first and second common electrodes **117a** and **117b** substantially parallel with the data lines **124**. The second portion **130b** of the pixel electrode **130** is disposed above the second common electrode **117b** overlapping the second common electrode **117b**. The width of the second portion **130b** of the pixel electrode **130** is smaller than that of the second common electrode **117b** by about 3 micrometers on both sides. The second portion **130b** of the pixel electrode **130** and the second common electrode **117b** form the supplementary storage capacitor **C2** with the gate insu-

lation layer **118** interposed therebetween. The gate insulation layer **118** acts as a dielectric layer in both the main storage capacitor **C1** and the supplementary storage capacitor **C2**. Since the source and drain electrodes **126** and **128** are spaced apart from each other, a portion of the ohmic contact layer **122** is removed using the source and drain electrodes **126** and **128** as a mask. Thus, a channel region is formed in the active layer **120** between the source and drain electrodes **126** and **128**.

[0043] As described herein before, according to the illustrated embodiment of the present invention, since the common line has a small width compared to the related art, the aperture ratio of the IPS-LCD device increases as much as the reduction in width of the common line. Furthermore, since the array substrate of the illustrated embodiment of the present invention has two storage capacitors, i.e., the main and supplementary storage capacitors, enough and sufficient capacitance can be achieved, thereby allowing the IPS-LCD device to have high resolution and high quality of displayed images.

[0044] It will be apparent to those skilled in the art that various modifications and variation can be made in the method of manufacturing a thin film transistor of the present invention without departing from the spirit or scope of the invention. Thus, it is intended that the present invention cover the modifications and variations of this invention provided they come within the scope of the appended claims and their equivalents.

1-12. (canceled)

13. A method of fabricating an array substrate for use in an IPS-LCD device, comprising:

forming a gate line, a gate electrode, a common line and first and second common electrode on a substrate using a first metal layer, wherein the gate and common lines are disposed in a first direction;

forming a gate insulation layer on entire surface of the substrate to cover the first metal layer;

forming an active layer on the gate insulation layer and an ohmic contact layer on the active layer using an amorphous silicon and impurity-doped amorphous silicon;

forming a data line, a source electrode, a drain electrode and a pixel electrode using a second metal layer, wherein the data line is disposed on the gate insulation layer in a second direction substantially perpendicularly crossing both the gate line and the common line to define a pixel area, wherein the source and drain electrode are disposed on the ohmic contact layer and spaced apart from each other, and wherein the pixel electrode is disposed on the gate insulation layer and includes a first portion that is disposed between the first and second common electrodes, a second portion that is disposed overlapping the second common electrode, and a third portion that is disposed above the common line; and

forming a thin film transistor at a crossing of the gate and data lines, the thin film transistor having of the gate electrode, the active layer, the ohmic contact layer, the source electrode and the drain electrode.

14. The method according to claim 13, wherein the third portion of the pixel electrode is disposed right above the common line.

15. The method according to claim 13, wherein a width of the second common electrode overlapped by the second portion of the pixel electrode is larger than that of the second portion of the pixel electrode by about 6 micrometers.

16. The method according to claim 13, wherein a distance between the first and second portions of the pixel electrode is larger than a distance between the first portion of the pixel electrode and the second common electrode by about 3 micrometers.

17. The method according to claim 13, wherein an end of the first portion is connected to the drain electrode of the thin film transistor.

18. The method according to claim 13, wherein the source electrode extends from the data line, the gate electrode extends from the gate line, the drain electrode extends from the first portion of the pixel electrode, the active layer is disposed right above the gate electrode, and the ohmic contact layer interposed between the active layer and the source and drain electrodes.

19. The method according to claim 13, wherein the first and second metal layers are formed of one of aluminum

(Al), aluminum alloy (Al alloy), chromium (Cr), molybdenum (Mo), and tungsten (W).

20. The method according to claim 13, wherein the common line and the first and second common electrodes are formed as one united body.

21. The method according to claim 13, wherein the pixel electrode and the drain electrode are formed as one united body.

22. The method according to claim 13, wherein the third portion of the pixel electrode and a portion of the common line with the gate insulation layer interposed therebetween form a first storage capacitor.

23. The method according to claim 13, wherein the second portion of the pixel electrode and the second common electrode with the gate insulation layer interposed therebetween form a second storage capacitor.

24. The method according to claim 13, wherein the gate and common lines are spaced apart from each other.

25. The method according to claim 13, wherein the first and second common electrodes substantially perpendicularly extend from the common line.

* * * * *

专利名称(译)	用于面内切换模式液晶显示装置的阵列基板及其制造方法		
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摘要(译)

本发明涉及IPS-LCD器件和制造用于IPS-LCD器件的阵列基板的方法，其增加高孔径比并提供大且足够的存储电容。由不透明金属形成的公共线被设计成具有较小的宽度以增加孔径比。像素电极的一部分与公共电极中的一个重叠，从而形成辅助存储电容器。结果，利用由像素电极的一部分和公共线的一部分构成的主存储电容器，本发明的阵列基板可以具有两个存储电容器。可以获得足够和令人满意的电容并且提高孔径比。

